

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449/PTO

(Use as many sheets as necessary)

Complete if Known

Application Number	N/A
Filing Date	Herewith
First Named Inventor	David Muller, et al.
Art Unit	N/A
Examiner Name	N/A
Attorney Docket Number	MULLER 7-7

Sheet	1	of	2	Attorney Docket Number	MULLER 7-7
-------	---	----	---	------------------------	------------

[illegible][illegible]

Examiner Signature	<i>Shah Stern</i>	Date Considered	3/4/2004
-----------------------	-------------------	--------------------	----------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

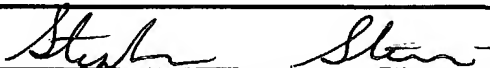
This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number	N/A
				Filing Date	Herewith
				First Named Inventor	David Muller, et al.
				Art Unit	N/A
				Examiner Name	N/A
Sheet	2	of	2	Attorney Docket Number	MULLER 7-7

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SSS		Kei-ichi Yamaguchi, Shigeru Imai, Naoto Ishitobi, Masashi Takemoto, Hidejiro Miki, and Masakiyo Matsumura; "ATOMIC-LAYER CHEMICAL-VAPOR-DEPOSITION OF SILICON DIOXIDE FILMS WITH AN EXTREMELY LOW HYDROGEN CONTENT"; June 1998, Applied Surface Science, Vol. 130-132, Pgs. 202-207.	
SSS		J.W. Klaus, O. Sneh, A.W. Ott and S.M. George; "ATOMIC LAYER DEPOSITION OF SiO ₂ USING CATALYZED AND UNCATALYZED SELF-LIMITING SURFACE REACTIONS"; June-Aug. 1999; World Scientific, Surface Review and Letters, Vol. 6, Nos. 3 & 4, Pgs. 435-448.	
SSS		D.A. Muller, T. Sorsch, S. Moccio, F.H. Baumann, K. Evans-Lutterodt & G. Timp; "THE ELECTRONIC STRUCTURE AT THE ATOMIC SCALE OF ULTRATHIN GATE OXIDES"; 24 June 1999; Macmillan Magazines Ltd., Nature, Vol. 399; Pgs. 758-761.	
SSS		Leonello Dori, Alexandre Acovic, Donelli J. DiMaria and Ching, Hsiang Hsu; "OPTIMIZED SILICON-RICH OXIDE (SRO) DEPOSITION PROCESS FOR 5-V-ONLY FLASH EEPROM APPLICATIONS"; June 1993, IEEE Electron Device Letters, Vol. 14, No. 6; Pgs. 283-285.	
SSS		J.B. Neaton, D.A. Muller and N.W. Ashcroft; "ELECTRONIC PROPERTIES OF THE Si/SiO ₂ INTERFACE FROM FIRST PRINCIPLES"; The American Physical Society, Volume 85, Number 6, 7 August 2002; Pgs. 1298-1301.	
SSS		David A. Muller, et al.; Serial No. 09/773,443 filed on October 2, 2003; "SILICON OXIDE BASED GATE DIELECTRIC LAYER".	

Examiner Signature		Date Considered	3/4/2004
--------------------	---	-----------------	----------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.